

ABSTRACT

STRUCTURE FOR RADIO-FREQUENCY APPLICATIONS

The invention relates to a structure (1) for radiofrequency applications comprising:

- a support substrate (2) of high-resistivity silicon comprising a lower part and an upper part (3) having undergone a p-type doping to a depth D;
- a mesoporous trapping layer (4) of silicon formed in the doped upper part (3) of the support substrate (2).

According to the invention, the structure (1) is noteworthy in that the depth D is less than 1 micron and the trapping layer (4) has a porosity rate of between 20% and 60%.

Figure 2